

Abstract of the Disclosure

A ROM embedded DRAM allows hard programming of ROM cells by shorting DRAM capacitor plates during fabrication. In one embodiment, the intermediate dielectric layer is removed and the plates are shorted with a conductor. In another embodiment, an upper conductor and dielectric are removed and a conductor is fabricated in contact with the DRAM storage plate. The memory allows ROM cells to be hard programmed to different data states, such as V_{cc} and V_{ss} .